PD -95636A

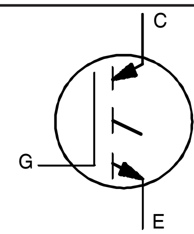
International
IOR Rectifier

IRG4IBC20WPbF

INSULATED GATE BIPOLAR TRANSISTOR

Features

- Designed expressly for Switch-Mode Power Supply and PFC (power factor correction) applications
- 2.5kV, 60s insulation voltage ⑥
- Industry-benchmark switching losses improve efficiency of all power supply topologies
- 50% reduction of Eoff parameter
- Low IGBT conduction losses
- Latest-generation IGBT design and construction offers tighter parameters distribution, exceptional reliability
- Industry standard Isolated TO-220 Fullpak™ outline
- Lead-Free



n-channel

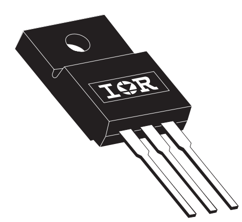
$V_{CES} = 600V$

$V_{CE(on)\ typ.} = 2.16V$

$@V_{GE} = 15V, I_C = 6.5A$

Benefits

- Lower switching losses allow more cost-effective operation than power MOSFETs up to 150 kHz ("hard switched" mode)
- Of particular benefit to single-ended converters and boost PFC topologies 150W and higher
- Low conduction losses and minimal minority-carrier recombination make these an excellent option for resonant mode switching as well (up to >>300 kHz)



TO-220 FULLPAK

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	12	A
I_C @ T_C = 100°C	Continuous Collector Current	6.0	
I_{CM}	Pulsed Collector Current ①	52	
I_{LM}	Clamped Inductive Load Current ②	52	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	200	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	34	W
P_D @ T_C = 100°C	Maximum Power Dissipation	14	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	——	3.7	°C/W
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	——	65	
Wt	Weight	2.0 (0.07)	——	g (oz)

06/11/2010

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 250µA	
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	V_{GE} = 0V, I_C = 1.0A	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.48	—	V/°C	V_{GE} = 0V, I_C = 1.0mA	
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.16	2.6	V	I_C = 6.5A	V_{GE} = 15V
		—	2.55	—		I_C = 13A	See Fig.2, 5
		—	2.05	—		I_C = 6.5A , T_J = 150°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-8.8	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA	
g_{fe}	Forward Transconductance ⑤	5.5	8.3	—	S	V_{CE} = 100 V, I_C = 6.5A	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 600V	
		—	—	2.0		V_{GE} = 0V, V_{CE} = 10V, T_J = 25°C	
		—	—	1000		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	26	38	nC	I_C = 6.5A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	3.7	5.5		V_{CC} = 400V See Fig.8
Q_{gc}	Gate - Collector Charge (turn-on)	—	10	15		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	22	—	ns	
t_r	Rise Time	—	14	—		T_J = 25°C
$t_{d(off)}$	Turn-Off Delay Time	—	110	160		I_C = 6.5A, V_{CC} = 480V
t_f	Fall Time	—	64	96		V_{GE} = 15V, R_G = 50Ω
E_{on}	Turn-On Switching Loss	—	0.06	—	mJ	Energy losses include "tail"
E_{off}	Turn-Off Switching Loss	—	0.08	—		See Fig. 9, 10, 14
E_{ts}	Total Switching Loss	—	0.14	0.2		
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	T_J = 150°C,
t_r	Rise Time	—	15	—		I_C = 6.5A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	—	150	—		V_{GE} = 15V, R_G = 50Ω
t_f	Fall Time	—	150	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	0.34	—	mJ	See Fig. 10, 11, 14
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	490	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	38	—		V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	8.8	—		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 13b)

② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10µH, R_G = 50Ω, (See fig. 13a)

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

⑥ t = 60s, f = 60Hz

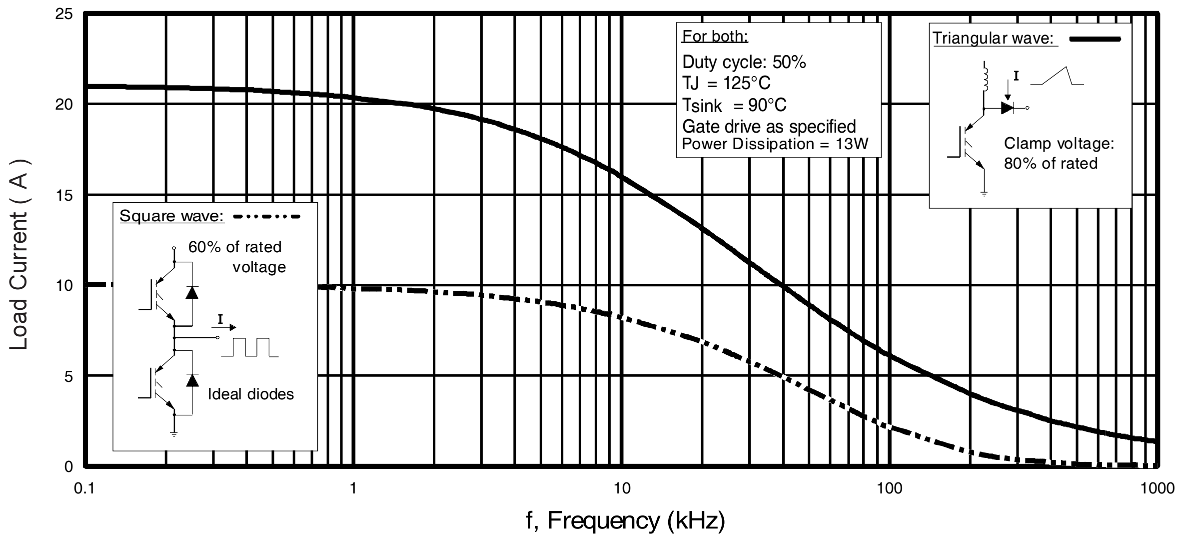


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

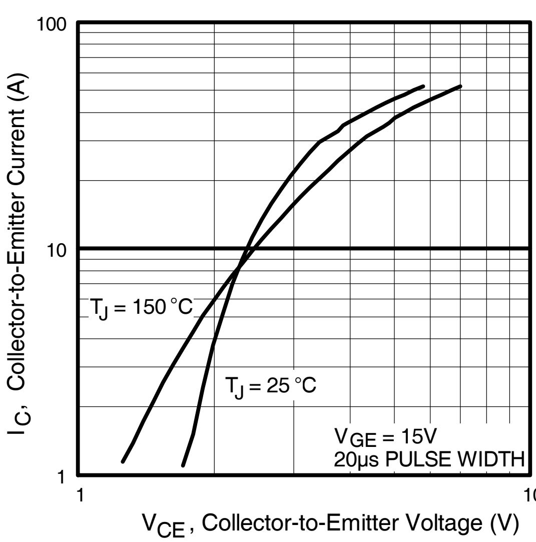


Fig. 2 - Typical Output Characteristics

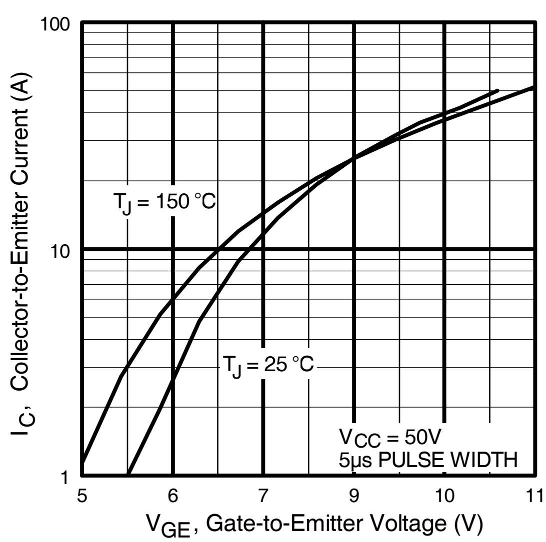


Fig. 3 - Typical Transfer Characteristics

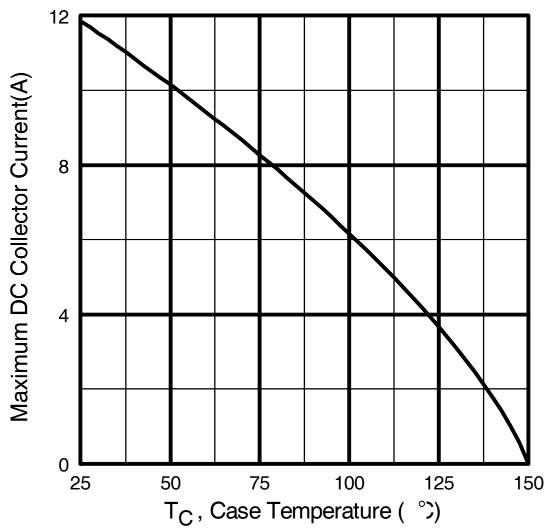


Fig. 4 - Maximum Collector Current vs. Case Temperature

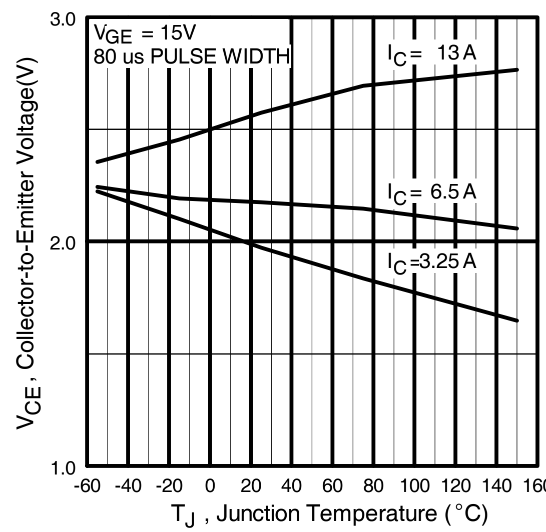


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

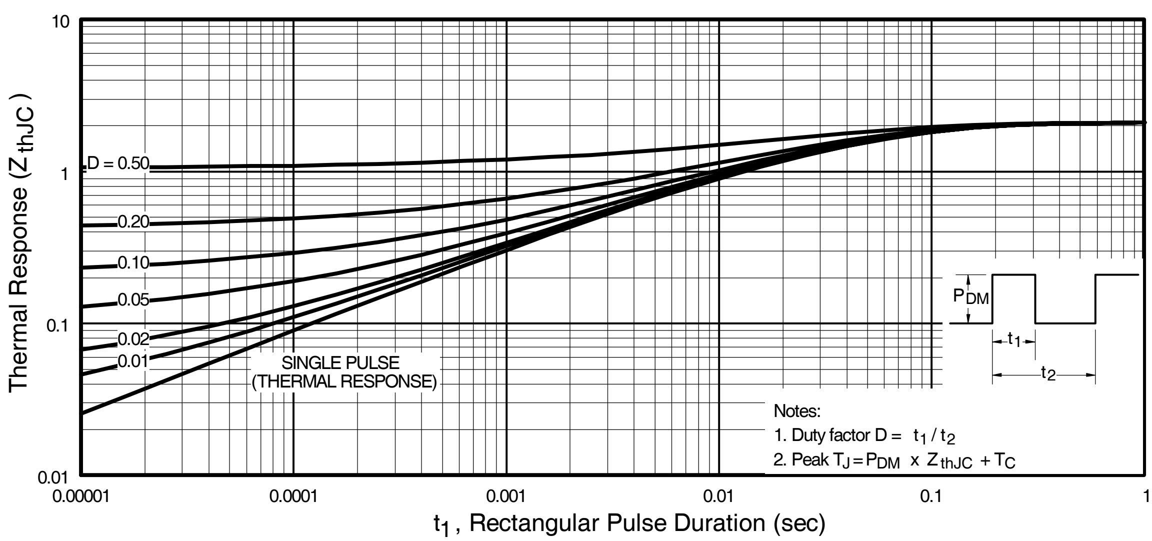


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

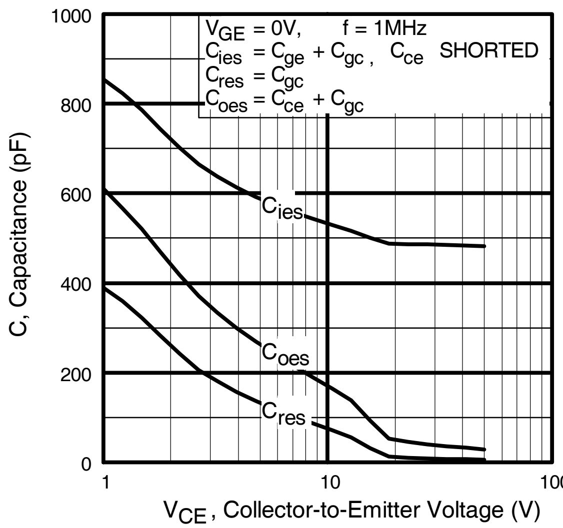


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

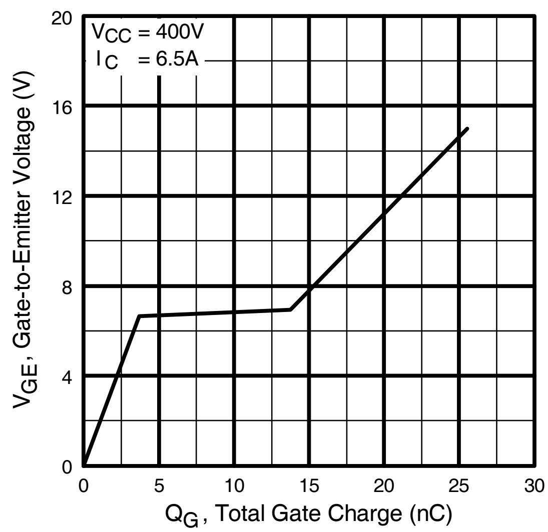


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

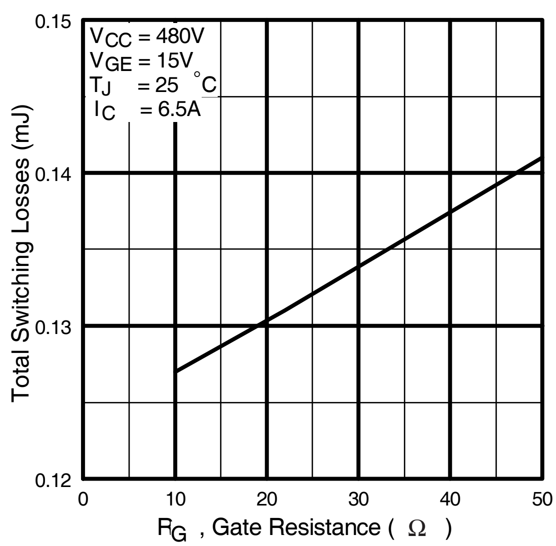


Fig. 9 - Typical Switching Losses vs. Gate Resistance

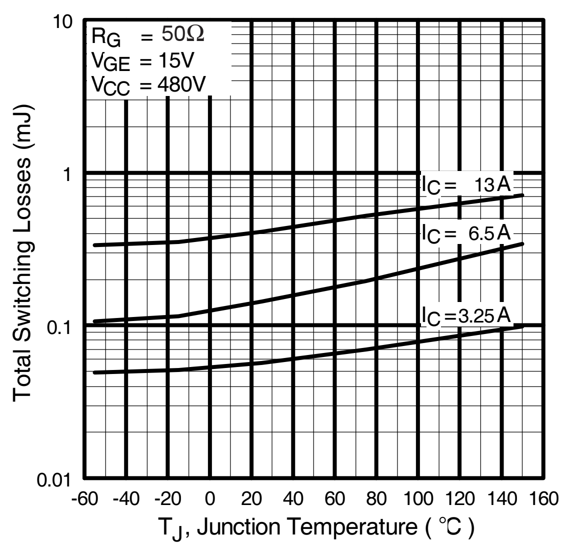


Fig. 10 - Typical Switching Losses vs. Junction Temperature

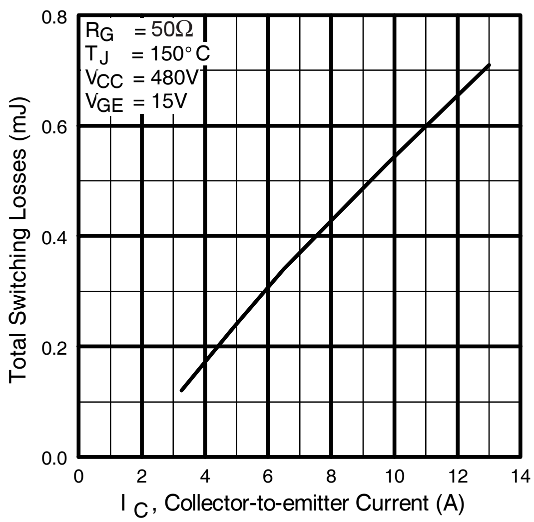


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

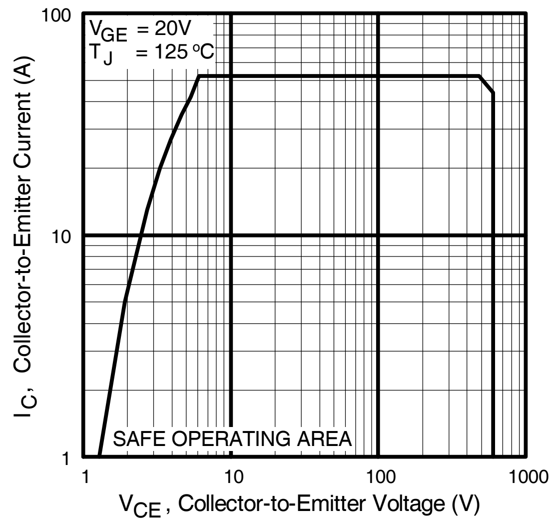


Fig. 12 - Turn-Off SOA

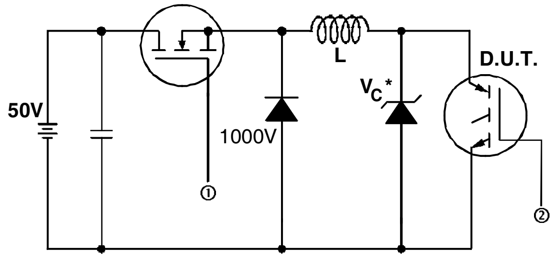


Fig. 13a - Clamped Inductive Load Test Circuit

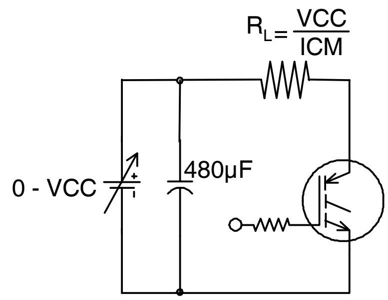


Fig. 13b - Pulsed Collector Current Test Circuit

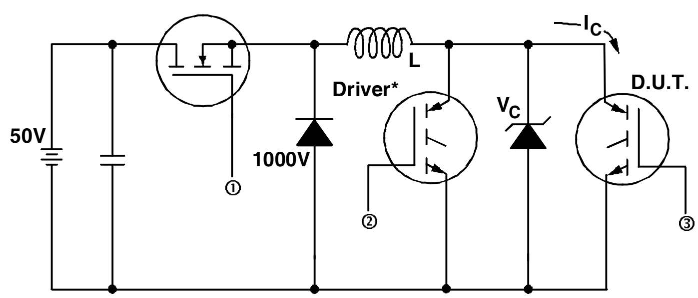


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., VC = 480V

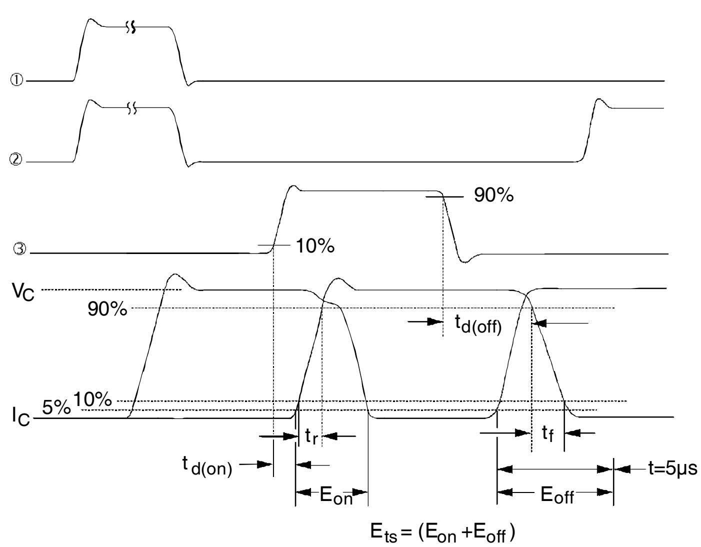
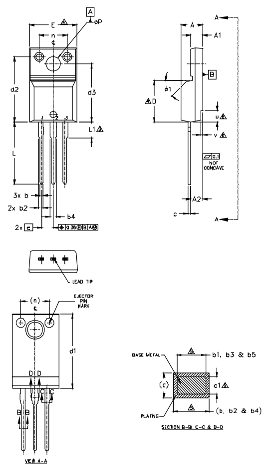


Fig. 14b - Switching Loss Waveforms

TO-220AB Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	
A1	2.57	2.83	.101	.111	
A2	2.51	2.93	.099	.115	
b	0.61	0.94	.024	.037	
b1	0.61	0.89	.024	.035	5
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	5
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	5
c	0.33	0.63	.013	.025	
c1	0.33	0.58	.013	.023	5
D	8.66	9.80	.341	.386	4
d1	15.80	16.13	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.30	12.93	.484	.509	
E	9.63	10.75	.379	.423	4
e	2.54 BSC		.100 BSC		
L	13.20	13.72	.520	.540	
L1	3.37	3.67	.122	.145	3
n	6.05	6.60	.238	.260	
øP	3.05	3.45	.120	.136	
u	2.40	2.50	.094	.098	6
v	0.40	0.50	.016	.020	6
ø1	–	45°	–	45°	

NOTES:

1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
7.0 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

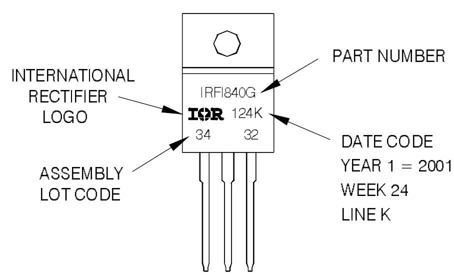
HEXFET
1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK
1.- GATE
2.- COLLECTOR
3.- EMITTER

TO-220AB Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24, 2001
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position indicates "Lead-Free"



TO-220AB Full-Pak package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Data and specifications subject to change without notice.

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